

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics²⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	2.3	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	-	62	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ³⁾	-	-	40	

Electrical characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1\text{mA}$	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=30\mu\text{A}$	2.0	3.0	4.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	0.02	1	μA
		$V_{DS}=18V, V_{GS}=0V, T_j=85^\circ\text{C}^{2)}$	-	1	20	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=86\text{A}$	-	4.3	5.2	m Ω

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Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	2280	2960	pF
Output capacitance	C_{oss}		-	560	730	
Reverse transfer capacitance	C_{rss}		-	17	39	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20\text{V}, V_{GS}=10\text{V},$ $I_D=86\text{A}, R_G=3.5\Omega$	-	9	-	ns
Rise time	t_r		-	11	-	
Turn-off delay time	$t_{d(off)}$		-	7	-	
Fall time	t_f		-	10	-	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=32\text{V}, I_D=86\text{A},$ $V_{GS}=0\text{ to }10\text{V}$	-	14	18	nC
Gate to drain charge	Q_{gd}		-	4	9	
Gate charge total	Q_g		-	29	37	
Gate plateau voltage	$V_{plateau}$		-	6.0	-	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25^\circ\text{C}$	-	-	86	A
Diode pulse current ²⁾	$I_{S,pulse}$		-	-	344	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=86\text{A},$ $T_j=25^\circ\text{C}$	-	0.9	1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=20\text{V}, I_F=50\text{A},$ $di_F/dt=100\text{A}/\mu\text{s}$	-	37	-	ns
Reverse recovery charge ²⁾	Q_{rr}		-	33	-	nC

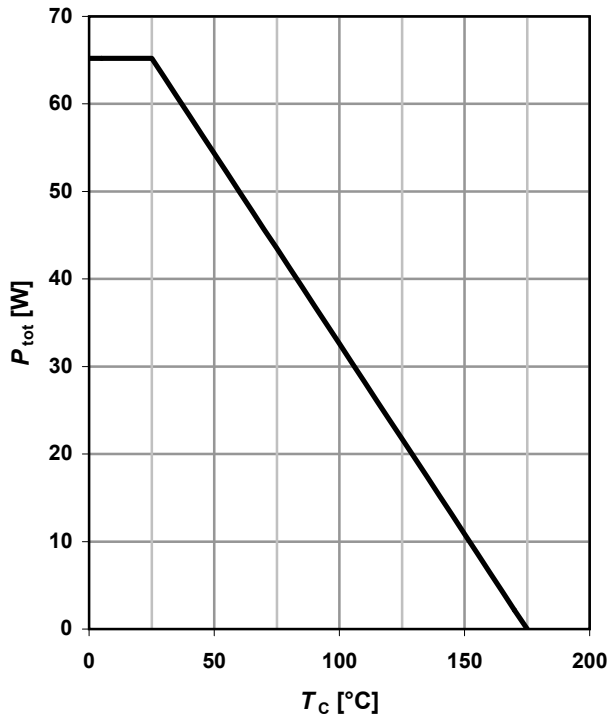
¹⁾ Current is limited by bondwire; with an $R_{thJC} = 2.3\text{K/W}$ the chip is able to carry 84A at 25°C.

²⁾ Defined by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

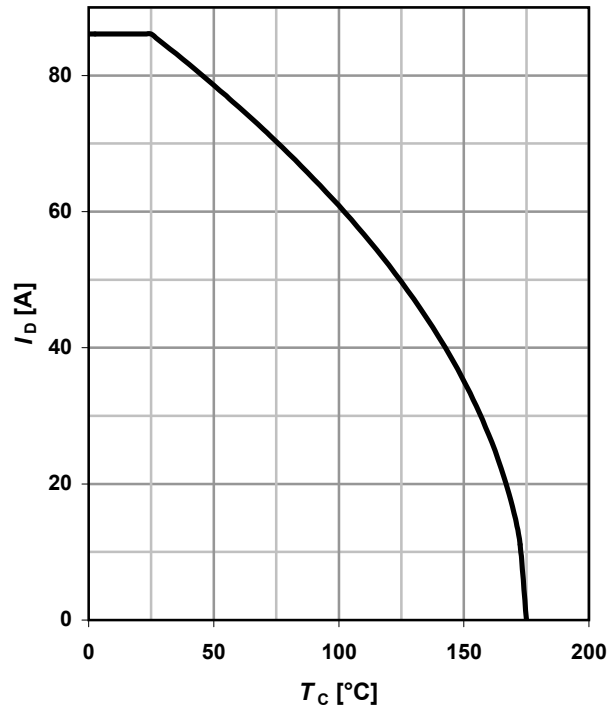
1 Power dissipation

$P_{tot} = f(T_C); V_{GS} \geq 6 V$



2 Drain current

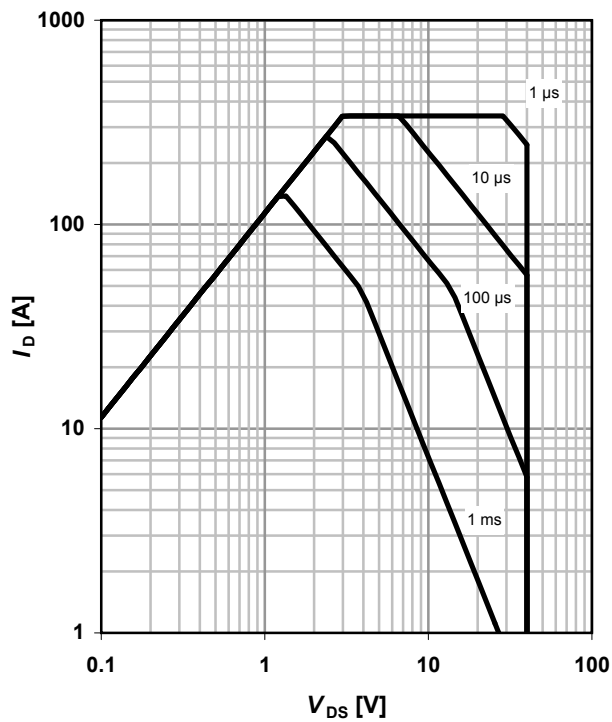
$I_D = f(T_C); V_{GS} \geq 6 V$



3 Safe operating area

$I_D = f(V_{DS}); T_C = 25\text{ °C}; D = 0$

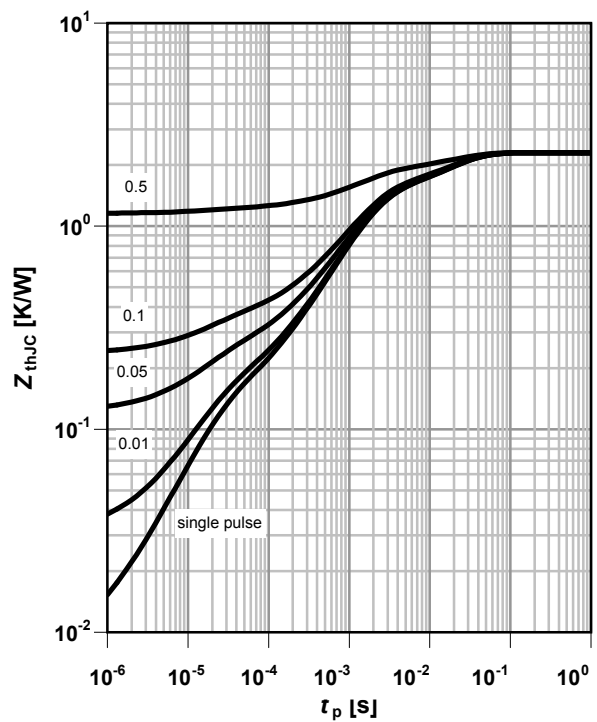
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

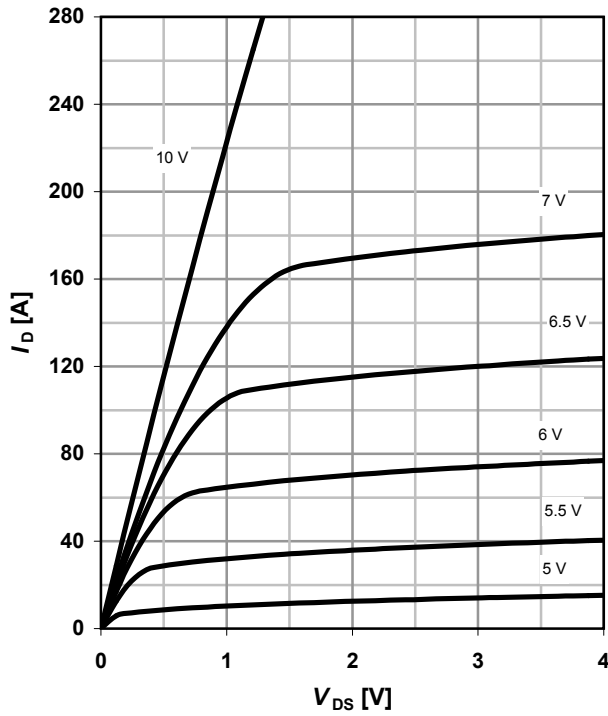
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

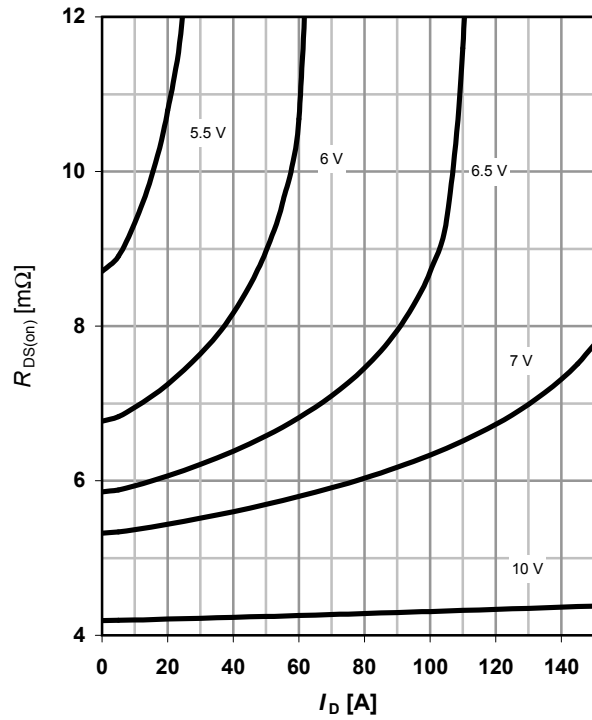
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

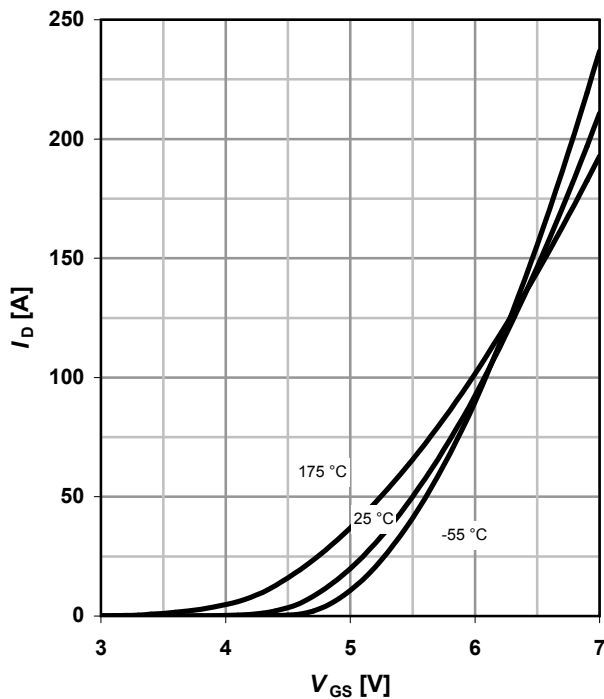
parameter: V_{GS}



7 Typ. transfer characteristics

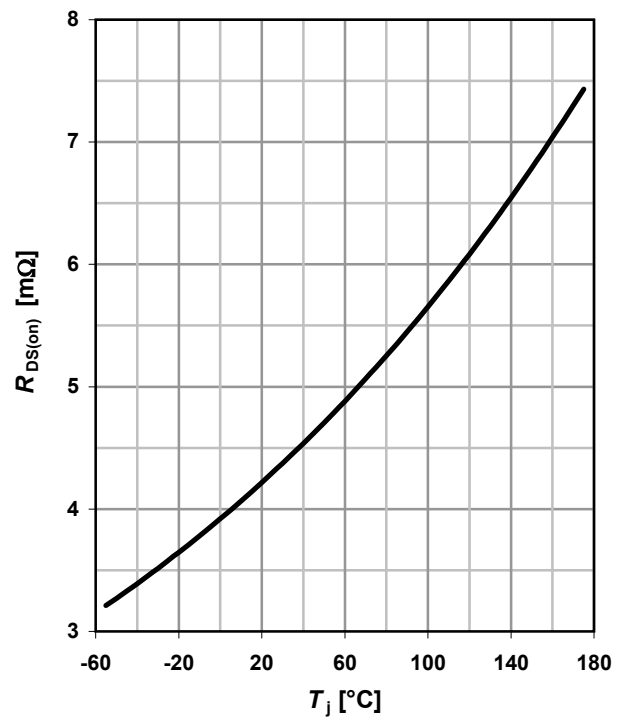
$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter: T_j



8 Typ. drain-source on-state resistance

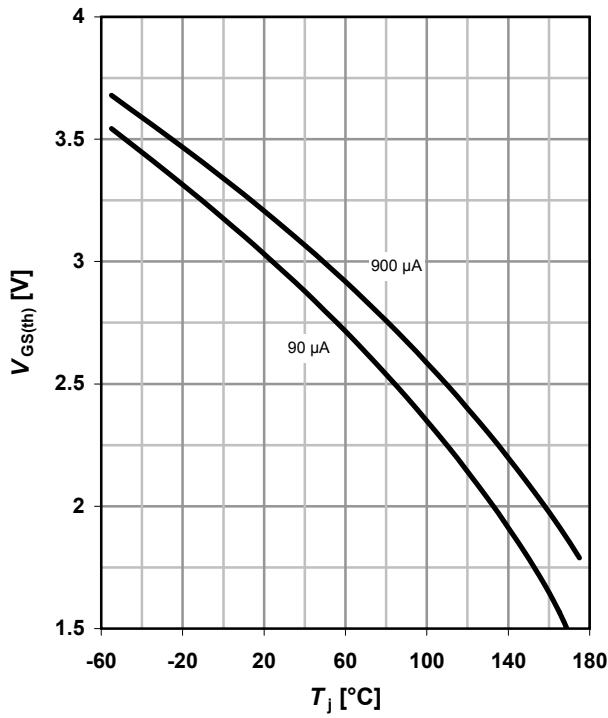
$R_{DS(on)} = f(T_j); I_D = 86\text{ A}; V_{GS} = 10\text{ V}$



9 Typ. gate threshold voltage

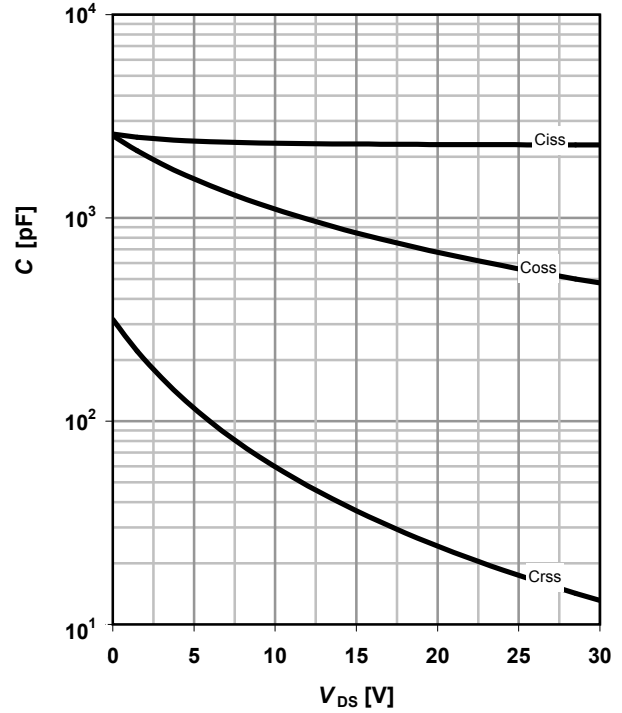
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

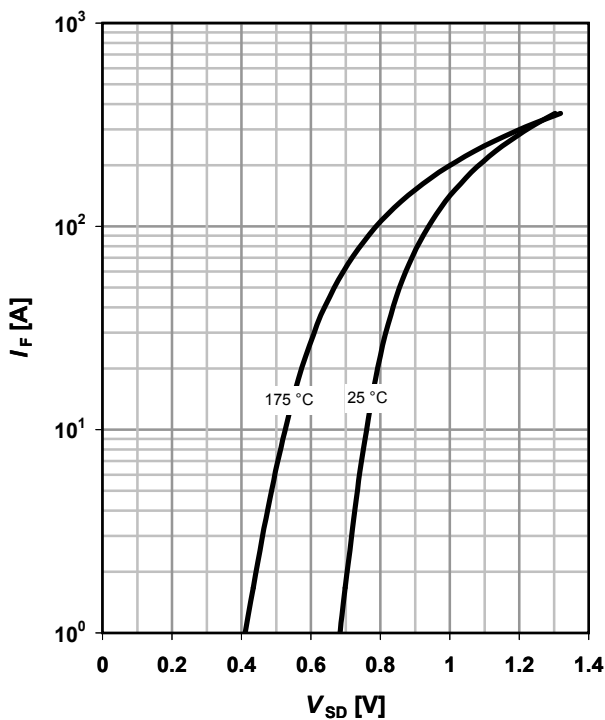
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



11 Typical forward diode characteristics

$I_F = f(V_{SD})$

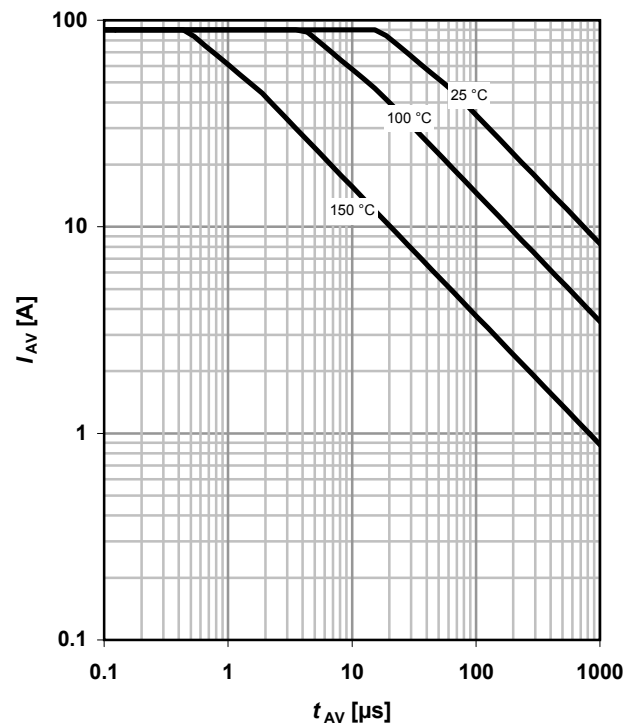
parameter: T_j



12 Avalanche characteristics

$I_{AS} = f(t_{AV})$

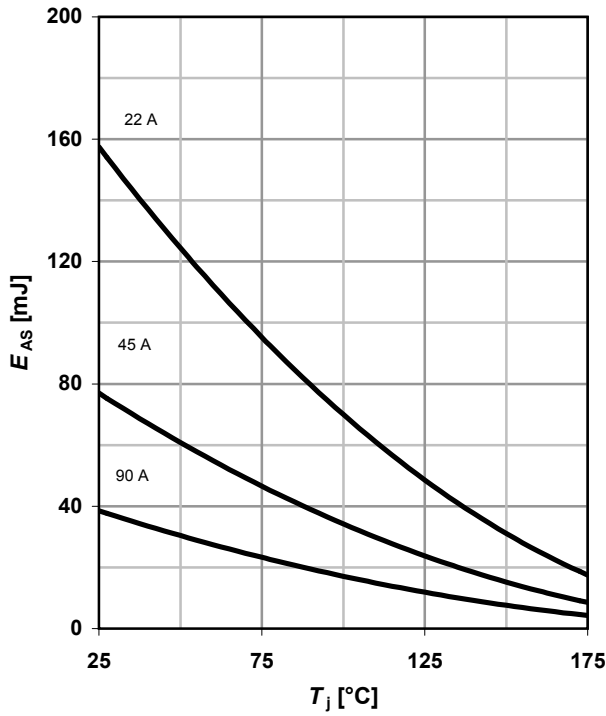
parameter: $T_{j(start)}$



13 Avalanche energy

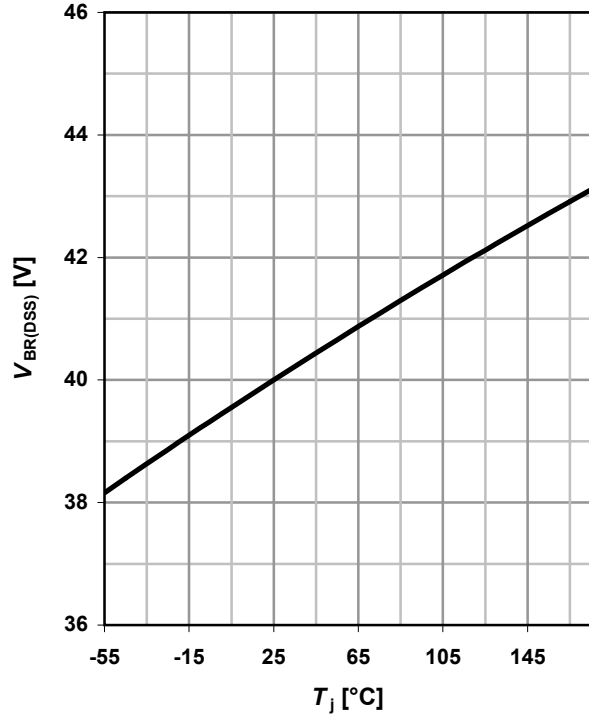
$$E_{AS} = f(T_j)$$

parameter: I_D



14 Drain-source breakdown voltage

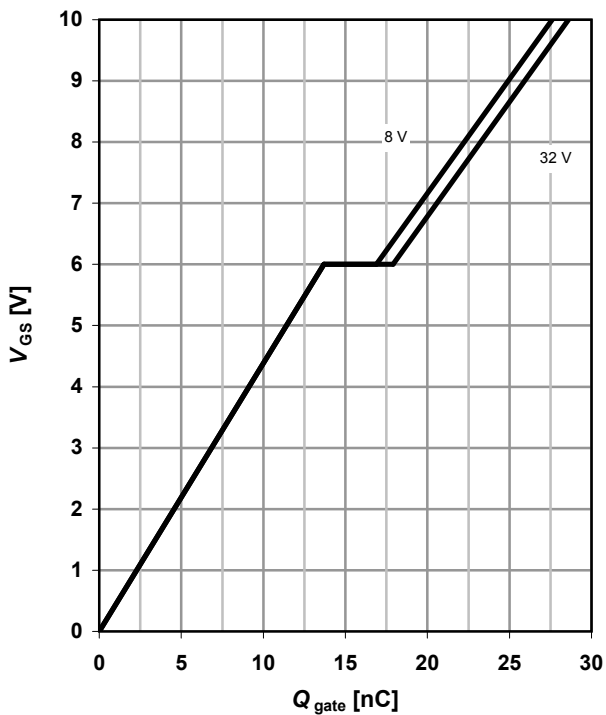
$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



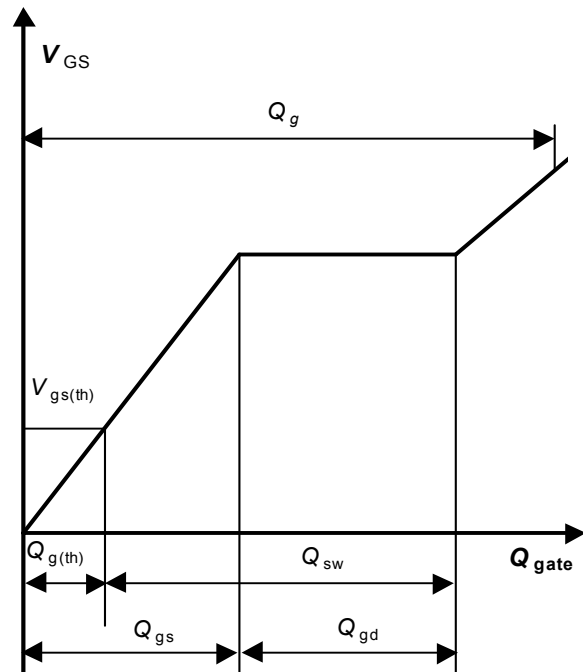
15 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 86 \text{ A pulsed}$$

parameter: V_{DD}



16 Gate charge waveforms



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Revision History

Version	Date	Changes
Revision 1.0	13.04.2010	Final Data Sheet